

-- 60. (New) A method for manufacturing a semiconductor device comprising steps of:

forming an initial semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma;

crystallizing said initial semiconductor film to obtain a crystalline semiconductor film; and

patterning said crystalline semiconductor film.

61. (New) A method according to claim 60, wherein said crystallizing is performed by crystallizing said initial semiconductor film by irradiating with an infrared ray or a laser light.

62. (New) A method according to claim 60, wherein said initial semiconductor film is crystallized without melting through a solid state.

63. (New) A method according to claim 60, wherein an oxide film of said semiconductor film is formed thereon by said oxygen plasma.

64. (New) A method for manufacturing a semiconductor device comprising steps of:

contacting a material for promoting crystallization to at least a part of an initial semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma; and

irradiating said semiconductor film with an infrared ray or a laser light.

65. (New) A method according to claim 64, wherein said initial semiconductor film is crystallized without melting through a solid state.

66. (New) A method according to claim 64, wherein an oxide film of said semiconductor film is formed thereon by said oxygen plasma. --